

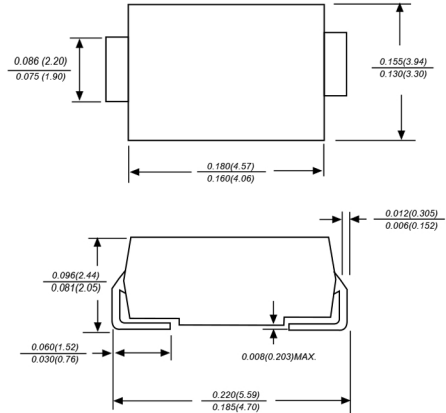
FEATURES

- Metal-Semiconductor junction with gard ring
- Epitaxial construction
- Low forward voltage drop
- High current capability
- The plastic material carries UL recognition 94V-0
- For use in low vlotage, high frequency inverters, free wheeling, and polarity protection applications

MECHANICAL DATA

- Case: Molded Plastic
- Polarity: Color band denotes cathode
- Weight :0.09 grams

DO-214AA



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.
Single phase half-wave 60Hz,resistive or inductive load,for capacitive load current derate by 20%.

CHARACTERISTICS	SYMBOL	SS52	SS53	SS54	SS55	SS56	SS58	SS510	SS515	SS520	UNIT
Maximum Recurrent Peak Reverse Voltage	VRRM	20	30	40	50	60	80	100	150	200	V
Maximum RMS Voltage	V _{RMS}	14	21	28	35	42	56	70	105	140	V
Maximum DC Blocking Voltage	V _{DC}	20	30	40	50	60	80	100	150	200	V
Maximum Average Forward Rectified Current 0.375" (9.5mm) Lead Lengths	I(AV)	5.0									A
Peak Forward Surge Current 8.3ms Single Half Sine-Wave Super Imposed on Rated Load(JEDEC Method)	I _{FSM}	100									A
Maximum Forward Voltage at 5.0A DC	V _F	0.55			0.7		0.85		0.95		V
Maximum DC Reverse Current @T _J =25℃ at Rated DC Bolcking Voltage @T _J =100℃	I _R	0.2 20			1.0 50						mA
Typical Junction Capacitance (Note1)	C _J	500			350						pF
Typical Thermal Resistance (Note2)	RθJA	15			10						℃/W
Operating Temperature Range	T _J	-55 to +150									℃
Storage Temperature Range	T _{STG}	-55 to +150									℃

NOTES: 1.Measured at 1.0 MHz and applied reverse voltage of 4.0V DC

2.Thermal resistance junction to ambient,

FIG. 1 – FORWARD CURRENT DERATING CURVE

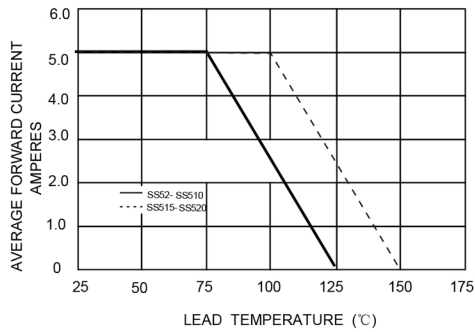


FIG. 2 – MAXIMUM NON-REPETITIVE SURGE CURRENT

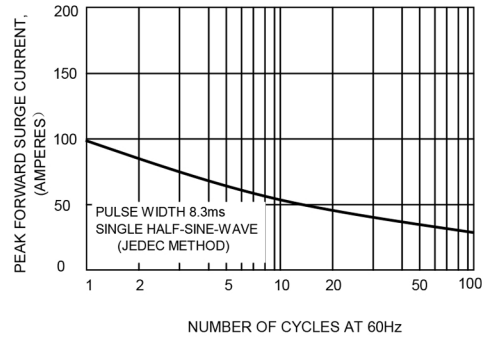


FIG. 3 – TYPICAL JUNCTION CAPACITANCE

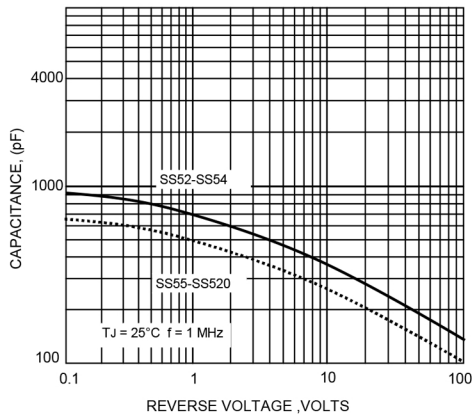


FIG. 4-TYPICAL FORWARD CHARACTERISTICS

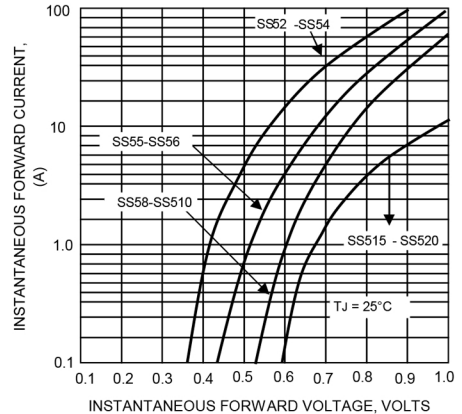


FIG. 2-TYPICAL REVER CHARACTERISTICS

